

R-C Thermal Model Parameters

DESCRIPTION

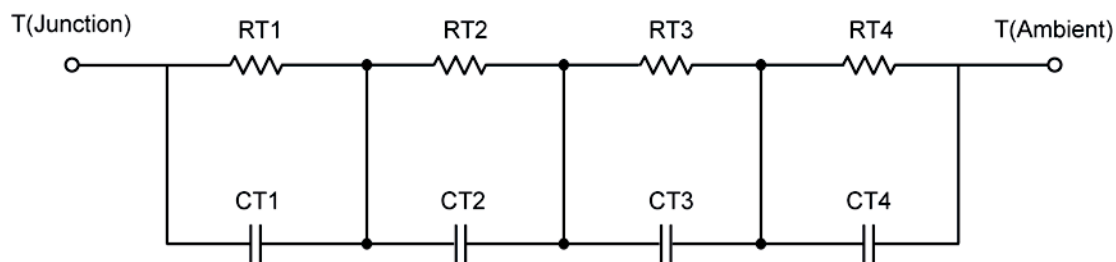
The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

Note:

For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK CONFIGURATION			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	37.8692	538.6494 m	N/A
RT2	9.6760	309.2872 m	N/A
RT3	13.7447	519.9868 m	N/A
RT4	3.7107	432.0766 m	N/A
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	2.4398	56.0952 m	N/A
CT2	109.5160 m	3.5975 m	N/A
CT3	1.2150	58.1325 m	N/A
CT4	13.5111 m	191.0312 m	N/A

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

R-C THERMAL MODEL FOR FILTER CONFIGURATION**R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RF1	3.4764	387.5324 m	N/A
RF2	11.8449	496.4702 m	N/A
RF3	24.7925	524.5205 m	N/A
RF4	24.8862	391.4769 m	N/A
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CF1	8.4494 m	3.2046 m	N/A
CF2	70.6034 m	18.4169 m	N/A
CF3	738.6042 m	13.1660 m	N/A
CF4	2.5610	21.9138 m	N/A

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

